



N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16342Q5A

FEATURES

- Optimized for 5V Gate Drive
- Resistance Rated at V_{GS} = 2.5V
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5mm x 6mm Plastic Package

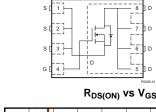
APPLICATIONS

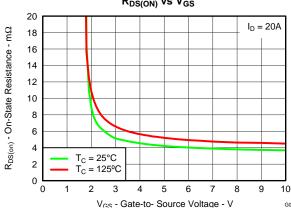
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control or Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5V gate drive applications.

Top View





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25	V			
Q_g	Gate Charge Total (4.5V)	6.8	nC			
Q_{gd}	Gate Charge Gate to Drain	Sate Charge Gate to Drain 1.2				
		$V_{GS} = 2.5V$	6.1	mΩ		
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V	4.3	mΩ		
		$V_{GS} = 8V$ 3.8		mΩ		
V_{th}	Threshold Voltage	0.85	V			

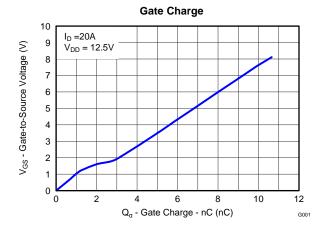
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16342Q5A	SON 5 x 6 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	٧
V_{GS}	Gate to Source Voltage	+10 / -8	٧
	Continuous Drain Current, T _C = 25°C	100	Α
I _D	Continuous Drain Current ⁽¹⁾	21	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	131	Α
P_D	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 40A$, $L = 0.1 mH$, $R_G = 25 \Omega$	80	mJ

- (1) Typical $R_{\theta JA}$ = $40^{\circ} C/W$ on $1 in^2$ Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static CI	haracteristics					
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{DS} = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}$, $I_{DS} = 250\mu A$	0.6	0.85	1.1	V
		$V_{GS} = 2.5V, I_{DS} = 20A$		6.1	7.8	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_{DS} = 20A$		4.3	5.5	$m\Omega$
		V _{GS} = 8V, I _{DS} = 20A		3.8	4.7	mΩ
9 _{fs}	Transconductance	V _{DS} = 15V, I _{DS} = 20A		91		S
Dynamic	Characteristics		•		· ·	
C _{ISS}	Input Capacitance			1050	1350	pF
Coss	Output Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		730	950	pF
C _{RSS}	Reverse Transfer Capacitance			53	69	pF
R _g	Series Gate Resistance			1.5	3	Ω
Qg	Gate Charge Total (4.5V)			6.8	7.1	nC
Q_{gd}	Gate Charge Gate to Drain	V 42 EV 1 20A		0.9		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_{D} = 20A$		1.9		nC
Qg(th)	Gate Charge at Vth			1.2		nC
Q _{OSS}	Output Charge	$V_{DS} = 13V$, $V_{GS} = 0V$	13.7			nC
t _{d(on)}	Turn On Delay Time			5.2		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V I_{D} = 20A$		16.6		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$		13.4		ns
t _f	Fall Time			3.1		ns
Diode C	haracteristics					
V _{SD}	Diode Forward Voltage	I _S = 20A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V 42V L 20A di/dt 200A/:	14.5			nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 20A$, $di/dt = 300A/\mu s$		20		ns

THERMAL CHARACTERISTICS

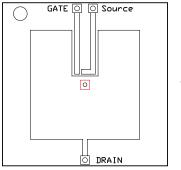
(T_A = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			1.2	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1)(2)			50	°C/W

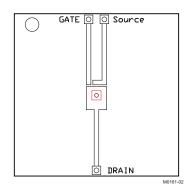
 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

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Max $R_{\theta JA} = 50^{\circ} C/W$ when mounted on 1 inch² of 2 oz. Cu.



Max $R_{\theta JA} = 123^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

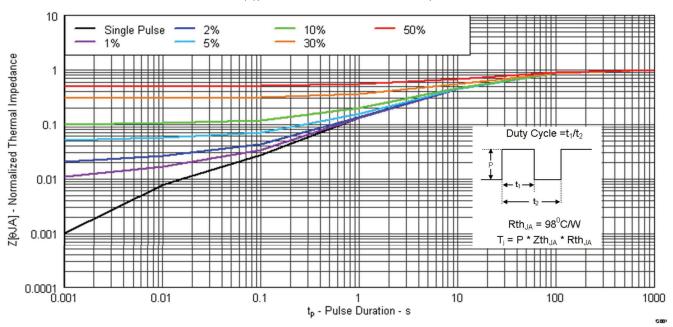


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

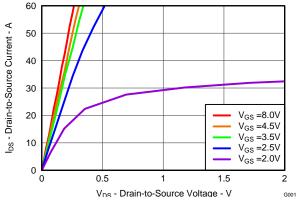


Figure 2. Saturation Characteristics

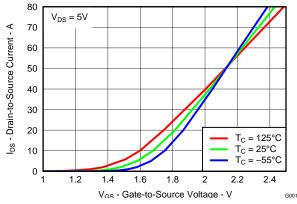


Figure 3. Transfer Characteristics

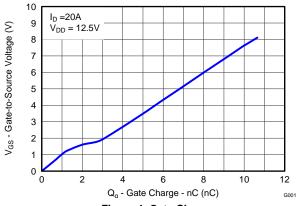


Figure 4. Gate Charge

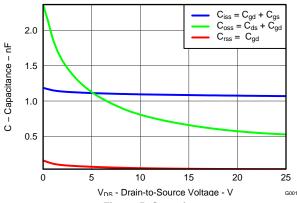


Figure 5. Capacitance

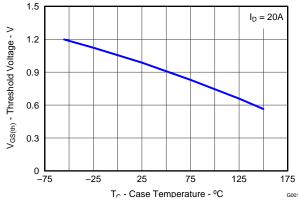


Figure 6. Threshold Voltage vs. Temperature

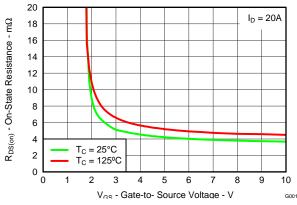


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

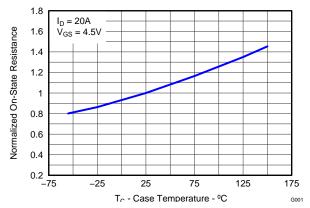


Figure 8. Normalized On Resistance vs. Temperature

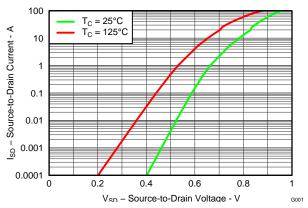


Figure 9. Typical Diode Forward Voltage

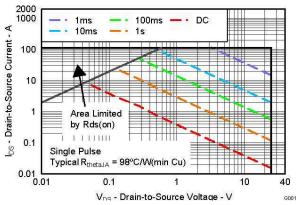


Figure 10. Maximum Safe Operating Area

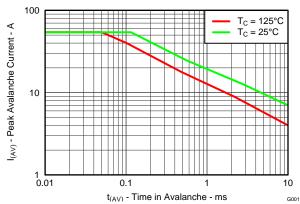


Figure 11. Single Pulse Unclamped Inductive Switching

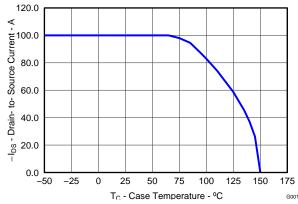
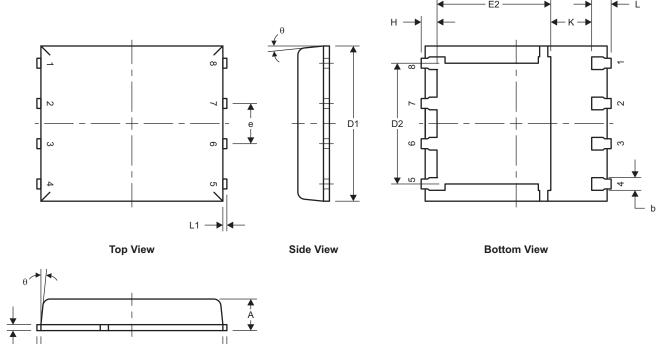


Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q5A Package Dimensions



E1 ______

Front View

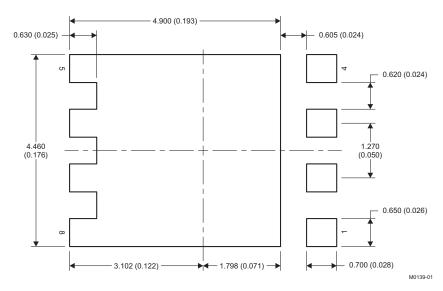
M0135-01

DIM	ı	MILLIMETERS	3	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.90	1.00	1.10	0.037	0.039	0.043	
b	0.33	0.41	0.51	0.000	0.000	0.002	
С	0.20	0.25	0.34	0.011	0.013	0.016	
D1	4.80	4.90	5.00	0.006	0.008	0.010	
D2	3.61	3.81	4.02	0.126	0.130	0.134	
E	5.90	6.00	6.10	_	_	_	
E1	5.70	5.75	5.80	0.065	0.069	0.071	
E2	3.38	3.58	3.78	0.126	0.130	0.134	
е	1.17	1.27	1.37	-	_	-	
Н	0.41	0.56	0.71	0.093	0.096	0.100	
K		1.10	•		•	•	
L	0.51	0.61	0.71	0.014	0.018	0.022	
L1	0.06	0.13	0.20	0.014	0.018	0.022	
θ	0°		12°	_	_	_	
θ	-	-	-	-	-	-	

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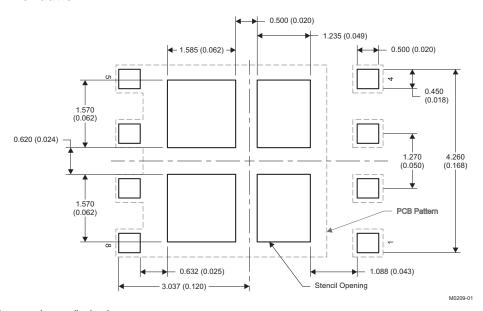


Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

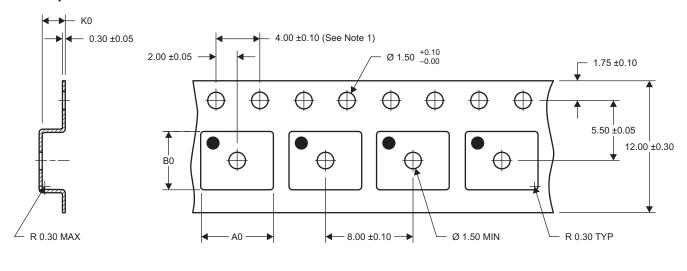
Stencil Recommendation



NOTE: Dimensions are in mm (inches).



Q5A Tape and Reel Information



A0 = 6.50 ±0.10 B0 = 5.30 ±0.10 K0 = 1.40 ±0.10

M0138-01

- NOTES: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
 - 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
 - 3. Material: black static-dissipative polystyrene
 - 4. All dimensions are in mm (unless otherwise specified)
 - 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

REVISION HISTORY

Changes from Original (February 2012) to Revision A

Page



PACKAGE OPTION ADDENDUM

28-Aug-2014

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CSD16342Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16342	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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28-Aug-2014

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